

APPARATUS FOR AND METHOD OF ETCHING AND CLEANING OBJECTS

Background of the invention

Field of the invention

The present invention relates to etching and cleaning apparatus and method for objects, and more particularly, to apparatus and method for batch processes for objects such as a semiconductor wafer or a liquid crystal display (LCD) substrate.

Description of Related Art

Etching technology is very important for compact and complicated substrates and is followed by a cleaning process.

For wet etching process a batch type is usually adopted since it can provide mass production and low production cost.

Fig. 1 schematically shows an etching apparatus of batch type according to a conventional art.

A vessel 10 containing substrates 12 has upper and lower openings 111 and 113 and is linked by many pipes. To the upper opening 111 are linked a first supplying pipe 10a and a first draining pipe 10d and to the lower opening 113 are linked a second supplying pipe 10b, a third supplying pipe 10c and a second draining pipe 10e. The first supplying pipe 10a is for supplying IPA(isoprophyl alcohol), the second supplying pipe 10b for supplying etching solution, and the third supplying pipe 10c for supplying D.I. (deionized) water. The first draining pipe 10d is for draining etching solution and D.I. water, and the second draining pipe 10e is for draining IPA and D.I. water.

The etching process and rinsing process using the apparatus is explained. First, through the second and the third supplying pipes 10b and 10c, etching solution and D.I.

water are supplied to the vessel 10 containing substrates 12, respectively. In some conditions only etching solution can be supplied, since D.I. water is for diluting the etching solution at this time.

Next, the substrates 12 are etched by the etching solution for some time.

5 Next, D.I. water is supplied through the third supplying pipe 10c so as to pull the mixture of etching solution and D.I. water to the upper opening 111 for draining through the first draining pipe 10d. At this time D.I. water cleans the substrates 12.

Finally, D.I. water is drained through the second draining pipe 10e and IPA is supplied to the vessel 10 in order to dry the substrates 12.

10 By the way, referring to Fig. 2, during draining the etching solution densities of the etching solution differ depending on the location of the interface of the etching solution and the D.I. water for cleaning. That is, in a certain instant during that process the density is high at the upper portion 12a of the vessel 10 and low at the middle portion 12b of the vessel, whereas at the lower portion 12c of the vessel 10 cleaning water such as D.I.
15 water is filled. This density difference results in non-uniform etching of the substrate 12 depending on the position of the substrate 12.

And during that time, while etching solution of high density is mixed with D.I. water for cleaning, an abnormal reaction such as electric reaction occurs. When two metal layers on the substrate are etched at one process, some metals such as aluminum lose their
20 electrons and some metals such as titanium get the electrons. Donor metal is over etched, and the donee is less etched, which deteriorates the quality of etching.

SUMMARY OF THE INVENTION

To overcome the problems described above preferred embodiments of the present

invention provide an apparatus for and a method of etching and cleaning objects which can achieve uniform etching.

A preferred embodiment of the present invention provides an apparatus for etching and cleaning objects, including: a vessel having an upper opening and a lower opening; a first supplying pipe connected to the upper opening of the vessel, the first
5 supplying pipe supplying dry gas; a second supplying pipe connected to the lower opening of the vessel, the second supplying pipe supplying etching solution; a third supplying pipe connected to the lower opening of the vessel, the third supplying pipe supplying cleaning solution; a first draining pipe connected to the upper opening of the vessel, the first
10 draining pipe draining the cleaning solution; and a second draining pipe connected to the lower opening of the vessel, the second draining pipe draining the etching solution and the dry gas.

It is preferred that the second draining pipe is directly and straightly connected to the lower opening of the vessel and has an inner diameter bigger than other pipes.

15 It is also preferred that in the second draining pipe a pump for draining etching solution is equipped.

According to another aspect of the invention, the method of etching and cleaning objects contained in a vessel, including: etching the objects by providing etching solution into the vessel; exiting the etching solution from the vessel by providing pressurized gas
20 into the vessel; cleaning the objects by providing cleaning solution into the vessel; and draining the cleaning solution from the vessel.

Draining the cleaning solution and exiting etching solution are processed through different draining pipes connected to the vessel.

The pressurized gas is preferably nitrogen gas.

The etching solution is preferably Oxalic acid solution or diluted Oxalic acid solution.

The cleaning solution is preferably deionized water.

Exiting the etching solution is preferably done with pumping the etching solution
5 out of the vessel.

The method may further include drying the objects by providing dry gas into the vessel after draining the cleaning solution. The dry gas may include IPA.

Advantages of the present invention will become more apparent from the detailed description given hereinafter. However, it should be understood that the detailed description
10 and specific examples, while indicating preferred embodiments of the invention, are given by way of illustration only, since various changes and modifications within the spirit and scope of the invention will become apparent to those skilled in the art from this detailed description.

BRIEF DESCRIPTION OF THE DRAWINGS

For a more complete understanding of the present invention and the advantages
15 thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which like reference numerals denote like parts, and in which:

Fig. 1 is a schematic view of an apparatus for etching and cleaning objects according to a conventional art;

Fig. 2 is a similar view to Fig. 1, illustrating density difference in the vessel
20 during the cleaning process while using the apparatus of Fig. 1; and

Fig. 3 is a schematic view of an apparatus for etching and cleaning objects according to an embodiment of the invention.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

Reference will now be made in detail to preferred embodiments of the present

invention, example of which is illustrated in the accompanying drawings.

A preferred embodiment of the present invention relates to a batch type apparatus for etching and cleaning the objects such as semiconductor wafers or substrates for LCDs.

The apparatus shown in Fig. 3 has a vessel 10 having upper and lower openings 110 and 112, which are connected to various pipes. The pipes connected to the upper opening 110 are a first supplying pipe 10a and a first draining pipe 10d, and the pipes connected to the lower opening 112 are second and third supplying pipes 10b and 10c and a second draining pipe 20. Though not illustrated in the drawings, there are valves in the pipes for selectively closing the pipes.

The first supplying pipe 10a is directly connected to the upper opening 110 of the vessel 10, and the first draining pipe 10d branches off from the main passage from the upper opening 110. The second draining pipe 20 is preferably straightly connected to the lower opening 112 of the vessel 10, and the second and third supplying pipes 10b and 10c branch off from the main passage from the lower opening 112 of the vessel 10. Since the second draining pipe 20 is straightly connected to the lower opening 112 of the vessel 10, draining through the second draining pipe 20 can be done without any bottleneck. The second draining pipe 20 can have an inner diameter bigger than those of other pipes, and have a pump "P" in order to help easy draining.

Through the first supplying pipe 10a pressurized gas and dry gas are supplied to the vessel 10. The pressurized gas needs to have a relatively low solubility to the etching solution and can be nitrogen gas. For dry gas IPA (isoprophyl alcohol) can be used, for dry process it has a gaseous phase having temperature of about 125???. Through the second supplying pipe 10b etching solution such as oxalic acid is supplied to the vessel 10. Through the third supplying pipe 10c cleaning solution such as deionized water is supplied

to the vessel 10.

The etching and cleaning process using the apparatus of the embodiment is explained.

First, through the second supplying pipe 10b etching solution is supplied to the vessel 10 having objects 12. At this time, in order to dilute the etching solution, cleaning solution such as D.I. water can be supplied to the vessel 10 at the same time.

Next, the objects are introduced under the etching process by the etching solution for a determined time.

Next, through the first supplying pipe 10a pressurized gases such as nitrogen gas is pushed into the vessel in order to drain or exit the etching solution or the etching solution mixed with the diluting solution through the second draining pipe 20. At this time, the second draining pipe 20 is open and the pump "P" is operated for easy draining. The pressurized gas is preferably chosen from the group consist of gases which does not react with the etching solution.

Next, the cleaning solution, for example D.I. water, is supplied into the vessel 10 through the third supplying pipe 10c in order to clean the objects and drained through the first draining pipe 10d.

Next, for dry process, IPA gas is supplied through the first supplying pipe 10a and drained through the second draining pipe 20.

According to the embodiment of the invention, since the cleaning solution and the etching solution does not make any interface during exiting the etching solution, there is no density difference of the etching solution through out the objects during the process, which also leads no electrical reaction during the process, leading to uniform etching for objects.